



Surface states and Fermi-level pinning on non-polar binary and ternary (Al,Ga)N surfaces

Lars Freter

Information

Band / Volume 84

ISBN 978-3-95806-644-1

Forschungszentrum Jülich GmbH
Ernst Ruska-Centrum für Mikroskopie und Spektroskopie mit Elektronen (ER-C)
Physik Nanoskaliger Systeme (ER-C-1/PGI-5)

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Schriften des Forschungszentrums Jülich
Reihe Information / Information

Band / Volume 84

ISSN 1866-1777

ISBN 978-3-95806-644-1

Contents

1	Introduction	5
2	Theory	9
2.1	One-dimensional tunneling effect of a single particle	10
2.2	Tunneling between materials with a different work function	13
2.3	Towards many-particle tunneling	15
2.3.1	Density of states	16
2.3.2	Bardeen approach of tunneling theory	17
2.3.3	Tersoff and Hamann approximation	20
2.4	Tunneling in semiconductors	23
2.4.1	Tip-induced band bending	24
2.4.2	Band bending due to surface states	26
2.5	Band structure and surface state position of III-nitride (10 $\bar{1}$ 0) according to DFT calculations	29
3	Experimental setup	33
3.1	Tip preparation	33
3.2	Sample preparation	35
3.3	Scanning tunneling microscope	36
3.4	Samples	38
3.4.1	Structure of sample A3782/A3787	38
3.4.2	Structure of the LED sample	40
4	Investigation of the influence of various physical parameters on tunnel currents simulated for <i>n</i>-type III-nitride (10$\bar{1}$0) semiconductor surfaces	43
4.1	Introduction	44
4.2	General remarks on the simulation packages used	45
4.3	Exponential dependence of the tunnel current on the tip-sample separation	47
4.4	Effects of sample parameters on the tunnel current	50
4.4.1	Variations in the band gap	50
4.4.2	Effect of the variation in the energy of surface states	52
4.4.3	Effect of the variation in the doping concentration	53

4.4.4	Electron affinity	56
4.5	Tip specific parameters	57
4.5.1	Tip radius	58
4.5.2	Tip work function	60
4.6	Conclusion	62
5	Investigation of Fermi-level pinning induced by intrinsic and extrinsic surface states at <i>n</i>- and <i>p</i>-type GaN (10$\bar{1}$0) surfaces	65
5.1	Experimental results	66
5.1.1	SIMS investigation	66
5.1.2	Microscopic characterization	71
5.1.3	Tunneling spectroscopy obtained at clean GaN (10 $\bar{1}$ 0) cleavage surfaces in UHV	73
5.1.4	Discussion of the origin of Fermi-level pinning	78
5.1.5	Tunneling spectroscopy on surfaces after exposure to ambient conditions	80
5.2	Discussion of the effect of air exposure	85
5.3	Conclusion	89
6	Intrinsic surface states of ternary (Al,Ga)N (10$\bar{1}$0) surfaces	91
6.1	Experiment	91
6.2	Experimental results	91
6.3	Discussion	97
6.3.1	Empty surface state of (Al,Ga)N	99
6.3.2	Empty surface state of AlN	102
6.3.3	Position of the empty surface state in DFT calculations	109
6.4	Conclusion	110
7	Summary	113
	Bibliography	117
	List of own publications	135
	Acknowledgment	137

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ISBN 978-3-95806-644-1

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